

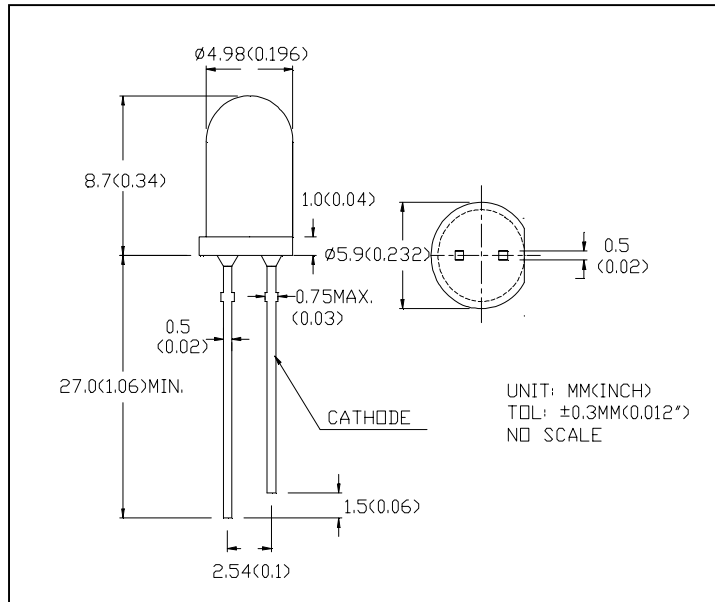
# MICRO ELECTRONICS

MWB51TA-DI  
MWB51TB-DI  
MWB51TK-DI

ULTRA HIGH  
BRIGHTNESS  
WHITE LED LAMP

## DESCRIPTION

MWB51TX-DI is an ultra high brightness InGaN/GaN white LED lamp encapsulated in a 5mm diameter clear transparent lens .



## ABSOLUTE MAXIMUM RATINGS

Power Dissipation @ Ta=25°C	125mW
Continuous Forward Current	30mA
Reverse Voltage	5V
Operating Temperature Range	-20 to +80°C
Storage Temperature Range	-30 to +100°C
Lead Soldering Temperature (1/16" from body)	260°C for 5 sec.

## ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	CONDITIONS
Forward Voltage	VF		3.5	4.5	V	IF=20mA
Reverse Breakdown Voltage	BVR	5			V	IR=100µA
Luminous Intensity	MWB51TA-DI MWB51TB-DI MWB51TK-DI	IV	2500 2000 1000	3800 3500 1800	mcd	IF=20mA
Viewing Angle	MWB51TA-DI MWB51TB-DI MWB51TK-DI	2θ 1/2	20 30 70		degree	IF=20mA
Chromaticity Coordinates	x y		0.30 0.30			IF=20mA

## CAUTION

REV : C

Static electricity and surge damages the LED ,It is recommended to use a wrist band or anti-eletrostatic glove when handling the LED . All devices,equipment and machinery must be properly grounded.



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